



150V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D T _C = +25°C
150V	310mΩ @ V _{GS} = 10 V	8.3A
	330mΩ @ V _{GS} = 5.0 V	8.0A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

Applications

- **Power Management Functions**
- **DC-DC Converters**

Features

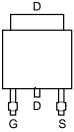
- Low R_{DS(ON)} ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

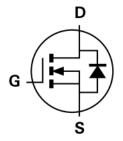
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.33 grams (Approximate)







Top View



Internal Schematic

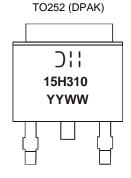
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN15H310SK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



☐ : = Manufacturer's Marking 15H310= Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 15 = 2015) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	150	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current, $V_{GS} = 10V$ $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$		I _D	8.3 5.2	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I _{DM}	10	Α	
Maximum Body Diode Continuous Current (note 5)		Is	2.6	Α
Avalanche Current, L = 3mH (Note 6)		I _{AS}	0.5	Α
Avalanche Energy, L = 3mH (Note 6)	E _{AS}	0.36	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation	T _C = +25°C	D-	32	W	
Total Fower Dissipation	T _C = +100°C	P_D	12	VV	
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	49	°C/W	
Thermal Resistance, Junction to Case		R ₀ JC	3.9	C/VV	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

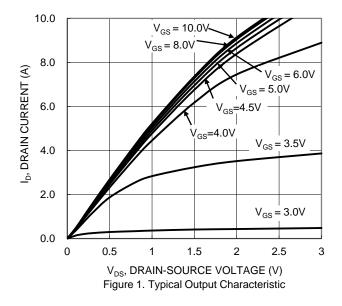
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	150	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	V _{DS} = 120V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	2.6	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		_	180	310	mΩ	$V_{GS} = 10V, I_D = 1.5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	195	330		V _{GS} = 5.0V, I _D = 1.0A	
		_	242	350		V _{GS} = 4.0V, I _D = 1.0A	
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	V _{GS} = 0V, I _S = 1.7A	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	Ciss	_	405	_		V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss	_	40	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	20	_			
Gate Resistance	R_{G}	_	2.88	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 5.0V)	Qg	_	4.6	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	8.7	_	nC	V 00V I 7.0A	
Gate-Source Charge	Q _{gs}	_	1.7	_	nc nc	$V_{DS} = 80V, I_{D} = 7.3A$	
Gate-Drain Charge	Q _{gd}	_	1.8	_			
Turn-On Delay Time	t _{D(ON)}	_	3.5	_			
Turn-On Rise Time	t _R		7.8	_		$V_{DD} = 50V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}		22	_	ns	$R_G = 25\Omega, I_D = 7.3A$	
Turn-Off Fall Time	t _F		11	_			
Reverse Recovery Time	t _{RR}	_	38	_	ns	I _F = 7.3A, di/dt = 100A/μs	
Reverse Recovery Charge	Q _{RR}	_	53	_	nC	I _F = 7.3A, di/dt = 100A/μs	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. Notes:

Guaranteed by design. Not subject to product testing.
 Short duration pulse test used to minimize self-heating effect.





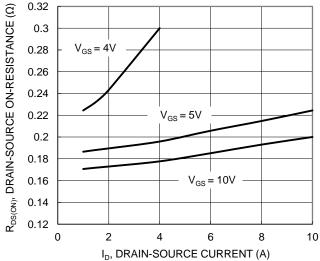


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

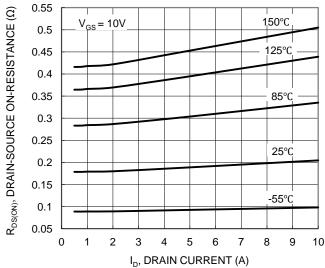
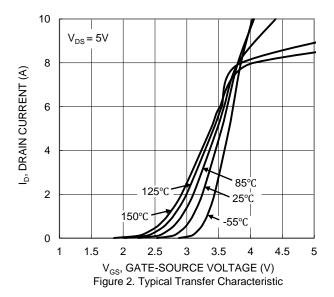
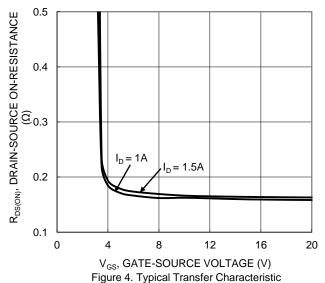


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





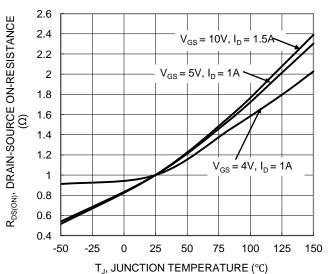


Figure 6. On-Resistance Variation with Junction
Temperature





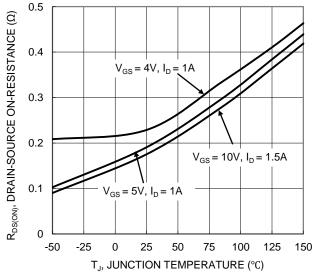
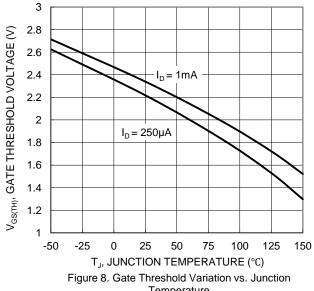


Figure 7. On-Resistance Variation with Junction Temperature



Temperature

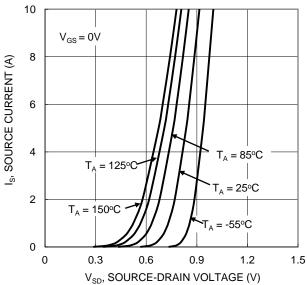
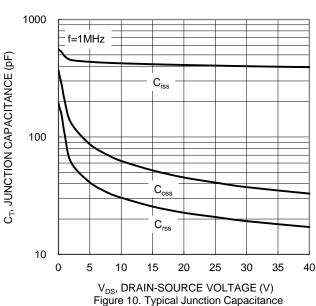
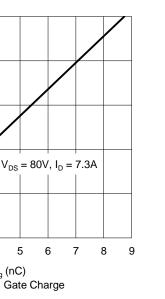


Figure 9. Diode Forward Voltage vs. Current





 $Q_a(nC)$ Figure 11. Gate Charge

5

6

7

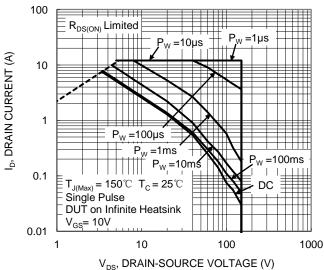


Figure 12. SOA, Safe Operation Area

2

3

10

8

6

4

2

0

 $V_{GS}(V)$



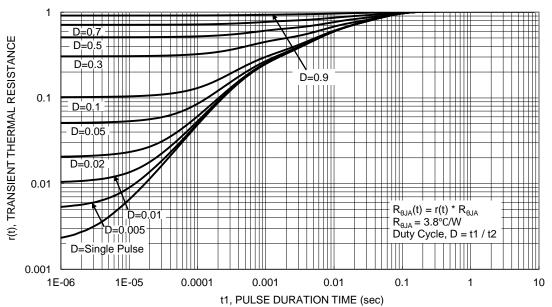
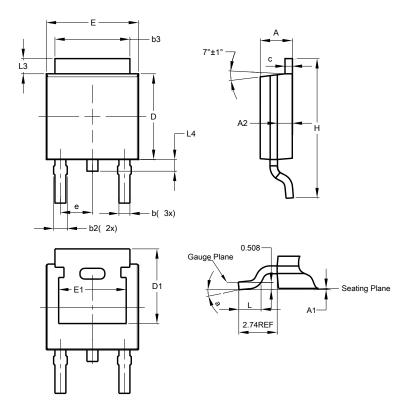


Figure 13. Transient Thermal Resistance



Package Outline Dimensions

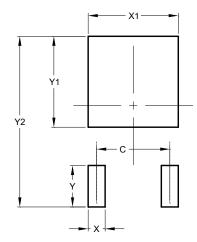
Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
C	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
I	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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